

HiPerFAST™ IGBT with Diode

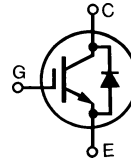
IXGK 50N50BU1
IXGK 50N60BU1

V_{CES}	I_{C25}	$V_{CE(sat)}$	t_{fi}
500 V	75 A	2.3 V	100ns
600 V	75 A	2.5 V	120ns

www.datasheet4u.com

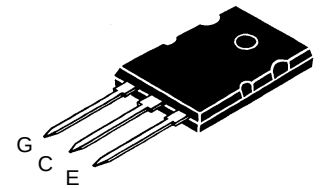
Combi Pack

Preliminary data



Symbol	Test Conditions	Maximum Ratings		
		50N50	50N60	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	500	600	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 1\text{ M}\Omega$	500	600	V
V_{GES}	Continuous	± 20	± 20	V
V_{GEM}	Transient	± 30	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	75	75	A
I_{C90}	$T_C = 90^\circ\text{C}$	50	50	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1 ms	200	200	A
SSOA (RBSOA)	$V_{GE} = 15\text{ V}$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 10\ \Omega$ Clamped inductive load, $L = 30\ \mu\text{H}$	$I_{CM} = 100$ @ 0.8 V_{CES}		A
P_C	$T_C = 25^\circ\text{C}$	300	300	W
T_J		-55 ... +150		$^\circ\text{C}$
T_{JM}		150		$^\circ\text{C}$
T_{stg}		-55 ... +150		$^\circ\text{C}$
M_d	Mounting torque (M4)	0.9/6	Nm/lb.in.	
Weight		10	g	
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300		$^\circ\text{C}$

TO-264 AA



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- International standard package JEDEC TO-264 AA
- High frequency IGBT and anti-parallel FRED in one package
- 2nd generation HDMOS™ process
- Low $V_{CE(sat)}$
 - for minimum on-state conduction losses
- MOS Gate turn-on
 - drive simplicity
- Fast Recovery Epitaxial Diode (FRED)
 - soft recovery with low I_{RM}

Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

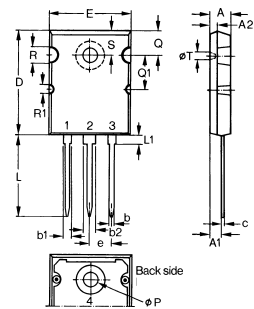
Advantages

- Space savings (two devices in one package)
- Easy to mount with 1 screw (isolated mounting screw hole)
- Reduces assembly time and cost
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 500\ \mu\text{A}$, $V_{GE} = 0\text{ V}$	50N50 50N60	500 600	V
$V_{GE(th)}$	$I_C = 500\ \mu\text{A}$, $V_{CE} = V_{GE}$	2.5		5.5 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0\text{ V}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		250 μA 15 mA
I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$			$\pm 100\text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}$, $V_{GE} = 15\text{ V}$	50N50BU1 50N60BU1		2.3 V 2.5 V

Symbol	Test Conditions	Characteristic Values (T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	I _C = I _{C90} , V _{CE} = 10 V, Pulse test, t ≤ 300 μs, duty cycle ≤ 2 % Remarks: Add capacitance from IXGH50N60B (DS95585B)	25	35	S
Q_g	I _C = I _{C90} , V _{GE} = 15 V, V _{CE} = 0.5 V _{CES}		200	nC
Q_{ge}			50	nC
Q_{gc}			70	nC
t_{d(on)}	Inductive load, T_J = 25°C I _C = I _{C90} , V _{GE} = 15 V, L = 100 μH, V _{CE} = 0.8 V _{CES} , R _G = R _{off} = 2.7 Ω Remarks: Switching times may increase for V _{CE} (Clamp) > 0.8 • V _{CES} , higher T _J or increased R _G		50	ns
t_{ri}			50	ns
t_{d(off)}			110	ns
t_{fi}		50N50	80	150 ns
E_{off}		50N60	150	ns
		50N50	1.8	mJ
		50N60	3.0	mJ
t_{d(on)}	Inductive load, T_J = 125°C I _C = I _{C90} , V _{GE} = 15 V, L = 100 μH V _{CE} = 0.8 V _{CES} , R _G = R _{off} = 2.7 Ω Remarks: Switching times may increase for V _{CE} (Clamp) > 0.8 • V _{CES} , higher T _J or increased R _G		50	ns
t_{ri}			60	ns
E_{on}			3	mJ
t_{d(off)}			200	ns
t_{fi}		50N50	100	ns
E_{off}		50N60	250	ns
		50N50	2.6	mJ
		50N60	4.2	mJ
R_{thJC}				0.42 K/W
R_{thCK}			0.15	K/W

TO-264 AA Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46	BSC	.215	BSC
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

Symbol	Test Conditions	Characteristic Values (T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
V_F	I _F = I _{C90} , V _{GE} = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			1.7 V
I_{RM}	I _F = I _{C90} , V _{GE} = 0 V, -di _F /dt = 480 A/μs V _R = 360 V T _J = 125°C I _F = 1 A; -di _F /dt = 200 A/μs; V _R = 30 V T _J = 25°C		19	33 A
t_{rr}			175	ns
			35	50 ns
R_{thJC}				0.75 K/W

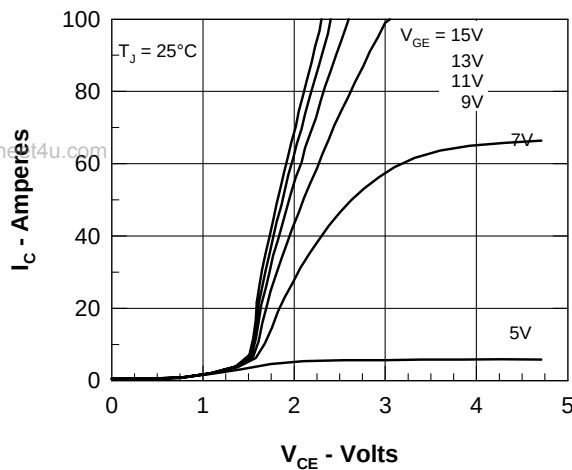


Figure 1. Saturation Voltage Characteristics

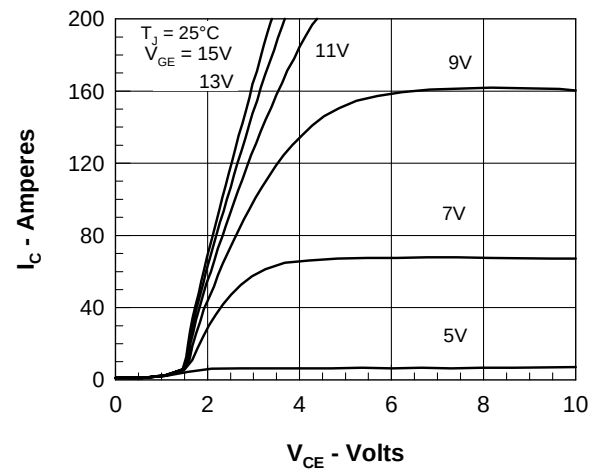


Figure 2. Extended Output Characteristics

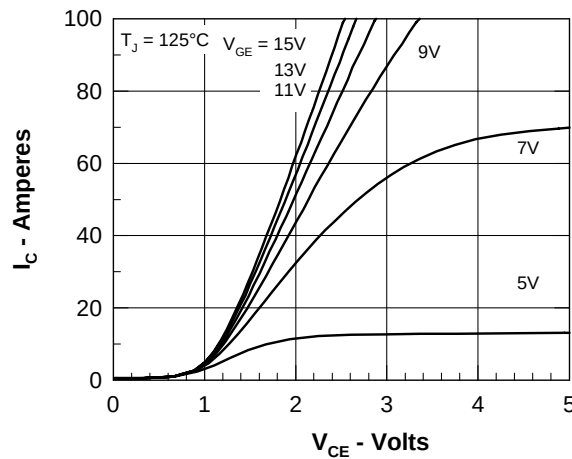


Figure 3. Saturation Voltage Characteristics

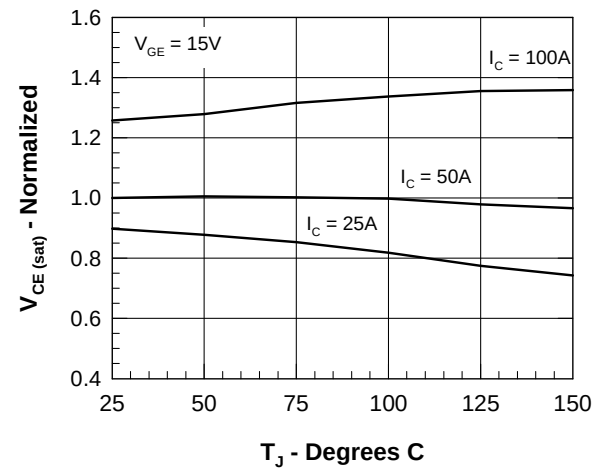
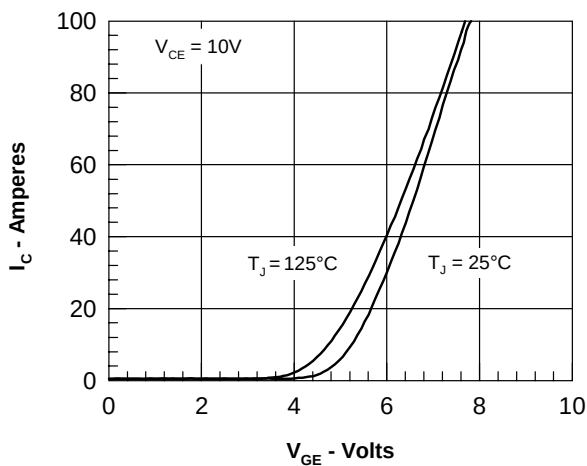

Figure 4. Temperature Dependence of $V_{CE(sat)}$


Figure 5. Admittance Curves

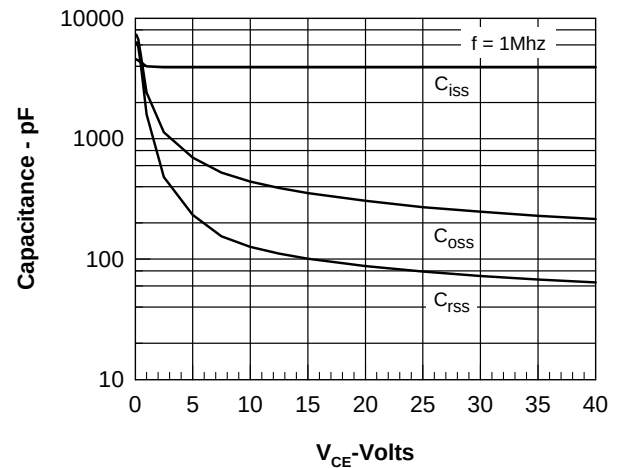


Figure 6. Capacitance Curves

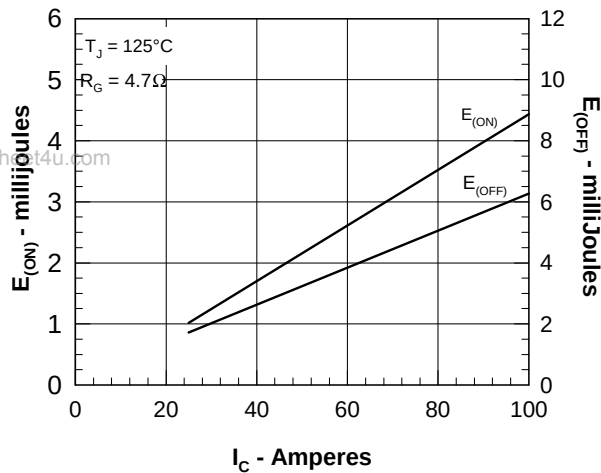


Figure 7. Dependence of E_{ON} and E_{OFF} on I_C .

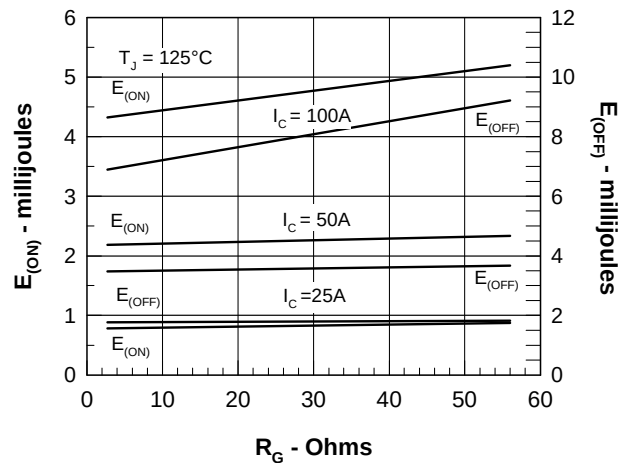


Figure 8. Dependence of E_{ON} and E_{OFF} on R_G .

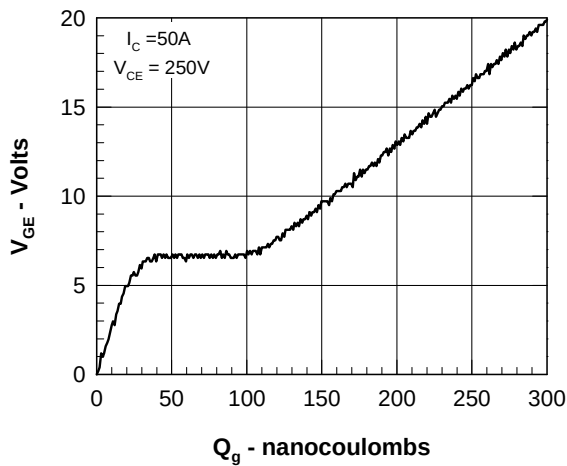


Figure 9. Gate Charge

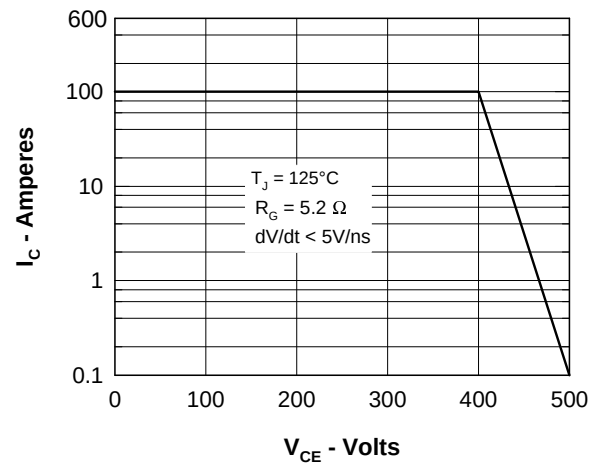


Figure 10. Turn-off Safe Operating Area

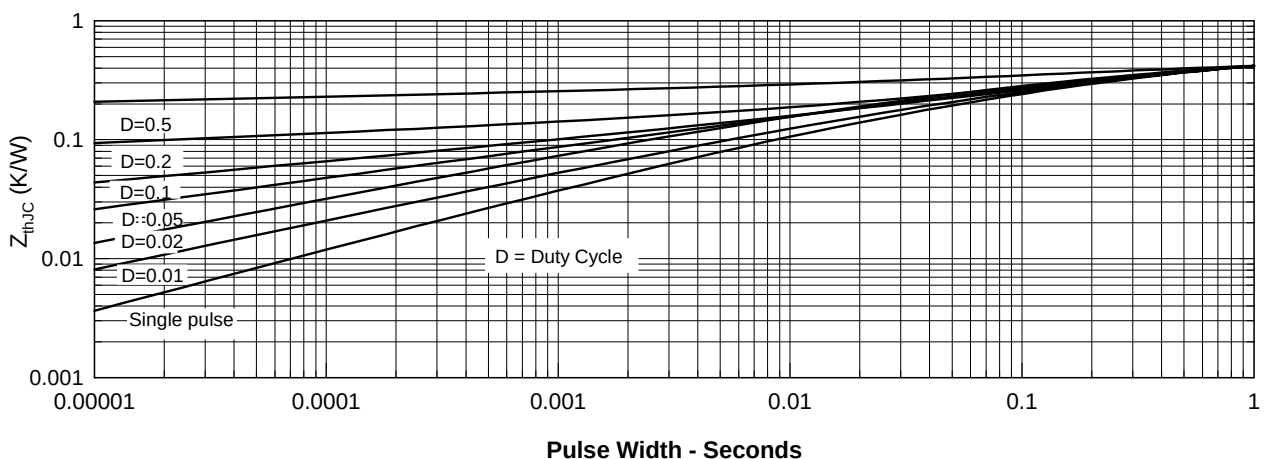


Figure 11. IGBT Transient Thermal Resistance

Fig. 12. Maximum Forward Voltage Drop

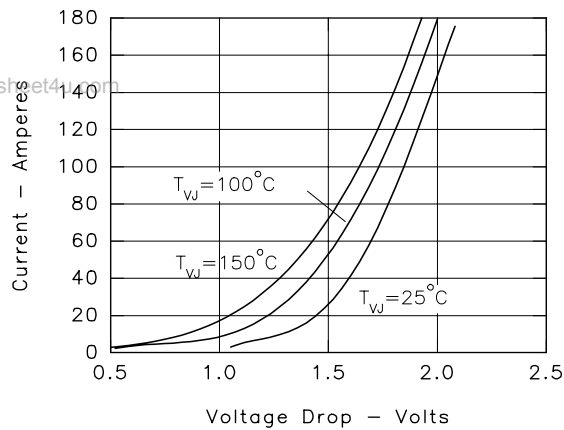
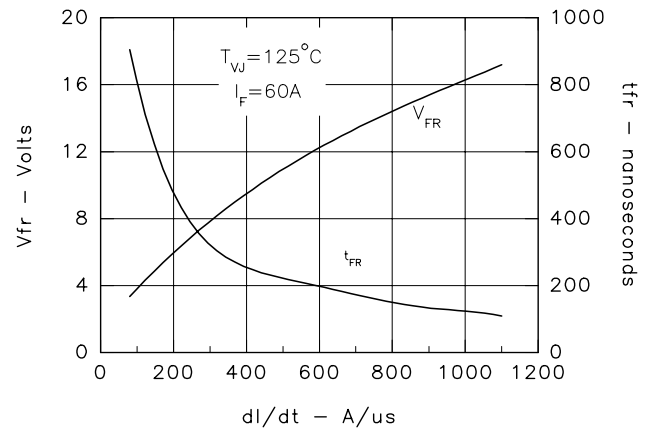
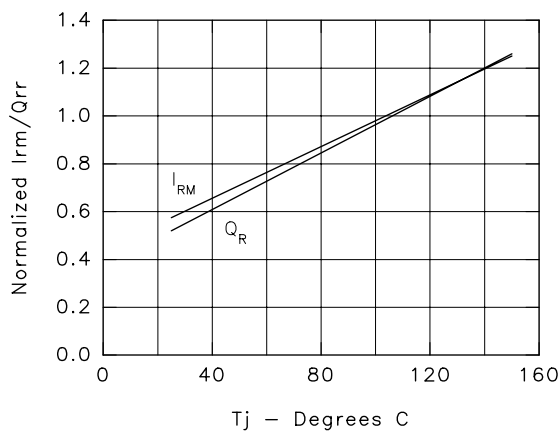
Fig. 13. Peak Forward Voltage V_{FR} and Forward Recovery Time t_{FR} Fig. 14. Junction Temperature Dependence of I_{RM} and Q_R 

Fig. 15. Maximum Reverse Recovery Charge

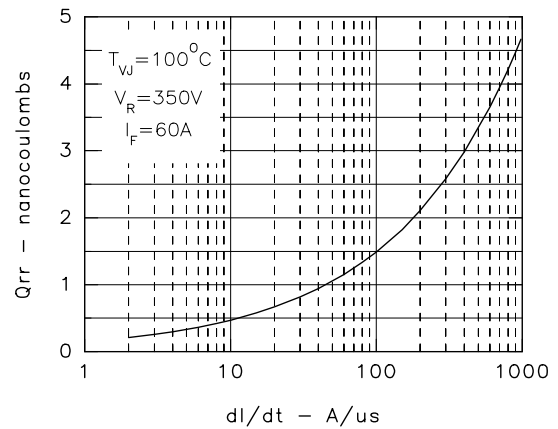


Figure 16. Peak Reverse Recovery Current.

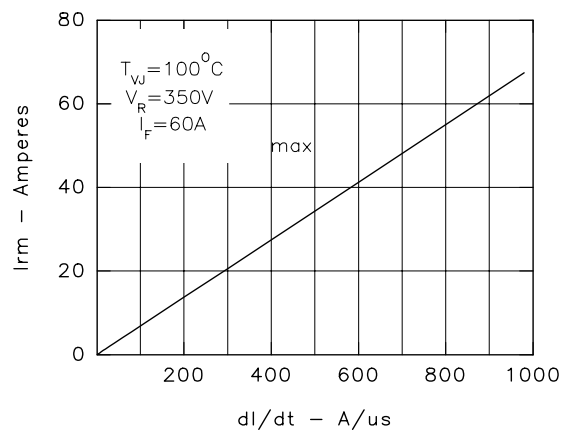
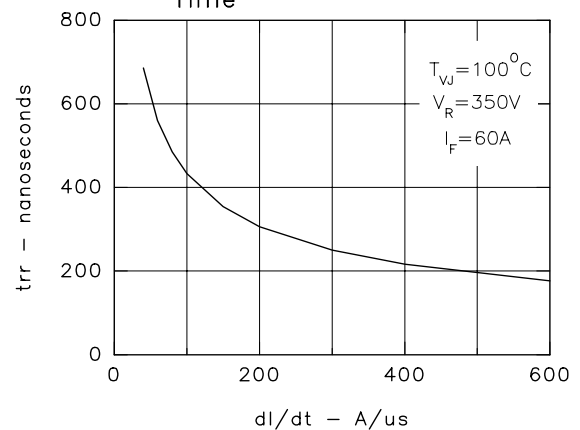


Fig. 17. Maximum Reverse Recovery Time



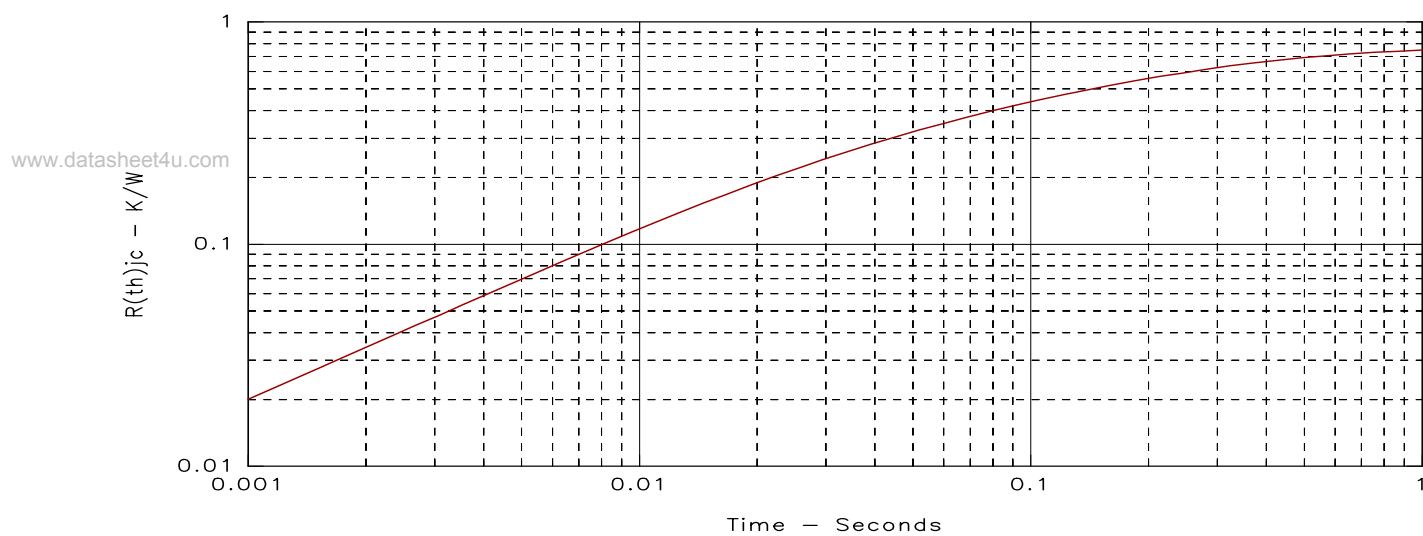


Fig. 18. Diode transient thermal resistance junction-to-case.